

Lecture 5

OUTLINE

- Bipolar Junction Transistor (BJT) (Cont'd)
 - BJT operation in saturation mode
 - PNP BJT
 - Examples of small signal models

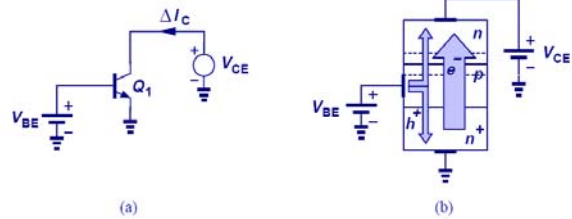
Reading: Chapter 4.5-4.6

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Bipolar Transistor in Saturation



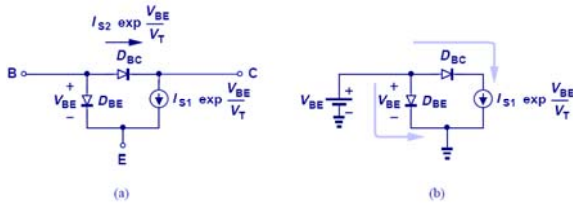
- When collector voltage drops below base voltage and forward biases the collector-base junction, base current increases and the current gain factor, β , decreases.

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Large-Signal Model for Saturation Region

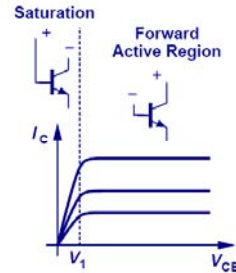


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Overall I/V Characteristics



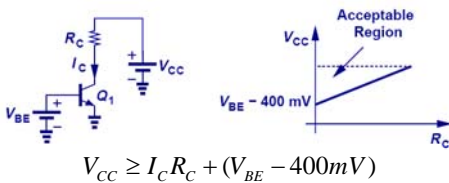
- The speed of the BJT also drops in saturation.

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Example: Acceptable VCC Region



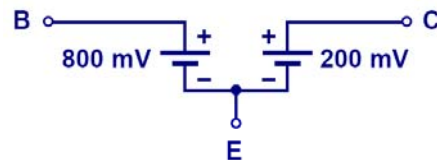
- In order to keep BJT at least in soft saturation region, the collector voltage must not fall below the base voltage by more than 400mV.
- A linear relationship can be derived for V_{CC} and R_C and an acceptable region can be chosen.

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Deep Saturation



- In deep saturation region, the transistor loses its voltage-controlled current capability and V_{CE} becomes constant.

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PNP Transistor

- With the polarities of emitter, collector, and base reversed, a PNP transistor is formed.
- All the principles that applied to NPN's also apply to PNP's, with the exception that emitter is at a higher potential than base and base at a higher potential than collector.

A Comparison between NPN and PNP Transistors

- The figure above summarizes the direction of current flow and operation regions for both the NPN and PNP BJT's.

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PNP Equations with Early Effect

$$I_C = I_S \exp \frac{V_{EB}}{V_T}$$

$$I_B = \frac{I_S}{\beta} \exp \frac{V_{EB}}{V_T}$$

$$I_E = \frac{\beta + 1}{\beta} I_S \exp \frac{V_{EB}}{V_T}$$

$$I_C = \left(I_S \exp \frac{V_{EB}}{V_T} \right) \left(1 + \frac{V_{EC}}{V_A} \right)$$

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Large Signal Model for PNP

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PNP Biasing

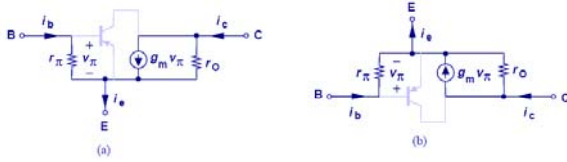
- Note that the emitter is at a higher potential than both the base and collector.

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Small Signal Analysis

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Small-Signal Model for PNP Transistor



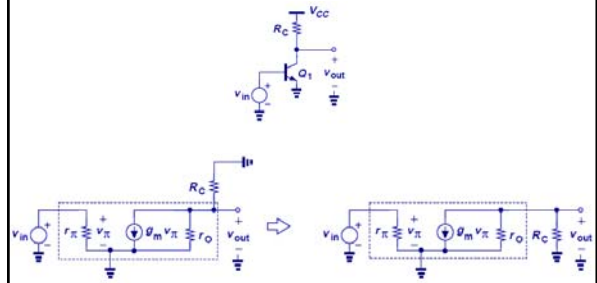
- The small signal model for PNP transistor is exactly IDENTICAL to that of NPN. This is not a mistake because the current direction is taken care of by the polarity of VBE.

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Small Signal Model Example I

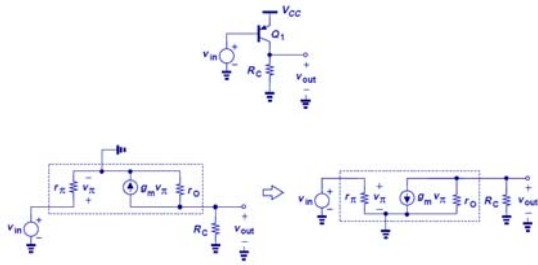


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Small Signal Model Example II



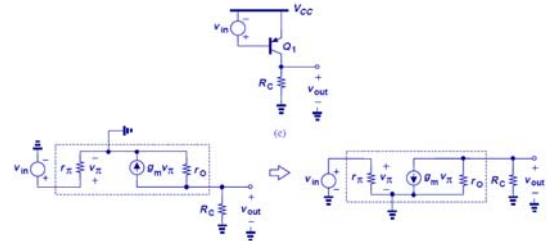
- Small-signal model is identical to the previous ones.

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Small Signal Model Example III



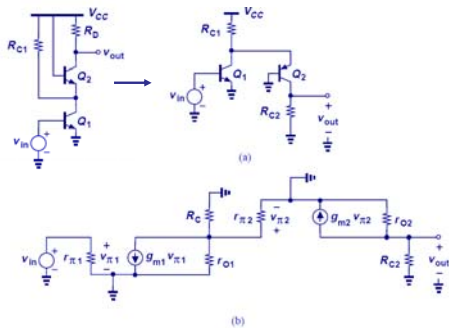
- Since during small-signal analysis, a constant voltage supply is considered to be AC ground, the final small-signal model is identical to the previous two.

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Small Signal Model Example IV



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